

- 1 (Previously Amended) An electronic component comprising:
a substrate; and
an airbridge located over the substrate and having at least a first layer and a second layer, wherein a first portion of the second layer is over the first layer,
wherein:
a gap exists between a portion of the airbridge and the substrate; and
a thickness of the second layer is less than a combined thickness of the first layer and the gap;
the airbridge is electrically conductive; and
the first layer of the airbridge is less resistive than the second layer of the airbridge.
2. (Original) The electronic component of claim 1 wherein:
the second layer is a passivation layer.
3. (Original) The electronic component of claim 1 wherein:
the second layer is harder than the first layer.
4. (Previously Cancelled)
5. (Original) The electronic component of claim 4 wherein:
the thickness of the second layer is less than fifty percent of the combined thickness of the first layer and the gap.
6. (Previously Amended) The electronic component of claim 1 wherein:
a second portion of the second layer is located underneath an edge of the first layer.
7. (Original) The electronic component of claim 1 wherein:
the second layer is absent underneath a center portion of a width of the airbridge.
8. (Original) The electronic component of claim 1 wherein:
a gap exists underneath a portion of the airbridge; and
the gap is unsealed underneath the portion of the airbridge.

9. (Original) The electronic component of claim 1 wherein:
the second layer of the airbridge has a compressive stress level of approximately
0 to 200 MegaPascals.
10. (Original) The electronic component of claim 1 wherein:
the airbridge further comprises:
a third layer underneath the first layer; and
the third layer is more resistive than the first layer.
11. (Original) The electronic component of claim 10 wherein:
the second layer is more resistive than the third layer.
12. (Original) The electronic component of claim 1 wherein:
the second layer of the airbridge is electrically conductive.
13. (Original) The electronic component of claim 1 wherein:
the second layer of the airbridge is electrically insulative.
14. (Previously Amended) A semiconductor component comprising:
a semiconductor substrate;
a semiconductor device supported by the semiconductor substrate;
a first electrically insulative layer overlying the semiconductor substrate and the
semiconductor device; and
an airbridge located over the semiconductor substrate, located over the first
electrically insulative layer, and electrically coupled to the semiconductor device,
wherein:
a gap exists between a portion of the airbridge and the first electrically
insulative layer;
the airbridge has a first electrically conductive layer; and
the airbridge has a second electrically insulative layer overlying the first
electrically conductive layer.

15. (Previously Amended) The semiconductor component of claim 14 wherein:

the second electrically insulative layer is a passivation layer harder than the first electrically conductive layer; and

the airbridge further comprises:

an electrically conductive barrier layer located underneath the first electrically conductive layer and more resistive than the first electrically conductive layer.

16. (Original) The semiconductor component of claim 15 wherein:

a thickness of the second electrically insulative layer is less than fifty percent of a combined thickness of the electrically conductive barrier layer, the first electrically conductive layer, and the gap.

17. (Original) The semiconductor component of claim 15 wherein:

the second electrically insulative layer is devoid of sealing the gap underneath the portion of the airbridge.

18. (Original) The semiconductor component of claim 14 wherein:

the second electrically insulative layer is absent underneath a center portion of a width of the airbridge.

19. (Original) The semiconductor component of claim 14 wherein:

the second electrically insulative layer has a compressive stress level of approximately 100 MegaPascals.

20. (Amended Herein) A method of manufacturing an electronic component comprising:

providing a substrate;

forming an electrically insulative layer over the substrate;

forming a first layer over the first electrically insulative layer to form a first portion of an airbridge;

forming a first portion of a second layer over the first layer to form a second portion of the airbridge over the substrate,

wherein:

the airbridge is electrically conductive; and

the first layer of the airbridge is less resistive than the second layer of the airbridge; and

forming a gap between the airbridge and the electrically insulative layer;

forming a semiconductor device at least partially located within the substrate;

and

wherein:

forming the first layer further comprises:

providing the first layer comprised of an electrically conductive material;

forming the second layer further comprises:

providing the second layer comprised of an electrically insulative material; and

forming the electrically insulative layer further comprises:

forming the electrically insulative layer over the semiconductor device.

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21. Cancelled Herein

22. - 33. Previously Cancelled

34. (Previously Amended) The method of claim 20 further comprising:
designing the airbridge to have a design width,
wherein:

forming the first layer further comprises:

forming the first layer to have a first layer width greater than the design
width; and

forming the second layer further comprises:

forming a second portion of the second layer underneath edges of the first
layer; and

keeping the second layer absent underneath a central portion of the first layer, the
central portion of the first layer having the design width.